

WHAT IS CLAIMED IS:

1. A photoelectric conversion device comprising:
a first-conductivity type first semiconductor
region located in a pixel region;

5 a second-conductivity type second semiconductor
region provided in the first semiconductor region and
capable of accumulating photoelectric carriers in a
floating state;

10 a wiring for electrically connecting the second
semiconductor region to a circuit element located
outside the pixel region; and

a conductor provided on the wiring located inside
the pixel region, via an insulator and capable of being
kept at a stated potential.

15

2. The photoelectric conversion device according
to claim 1, wherein the second semiconductor region is
an island-shaped region surrounded by the first
semiconductor region.

20

3. The photoelectric conversion device according
to claim 1, wherein the second semiconductor region has
a first part which is the island-shaped region
surrounded by the first semiconductor region and a
25 second part surrounding the first part and having a
lower impurity density than the first semiconductor
region.

4. The photoelectric conversion device according to claim 1, wherein the conductor is formed integrally with a light-screening layer provided for defining the pixel region.

5

5. The photoelectric conversion device according to claim 1, wherein the circuit element is an MOS transistor.

10

6. The photoelectric conversion device according to claim 1, wherein the circuit element comprises a resetting switch for resetting the potential of the second semiconductor region and an amplifying transistor for amplifying signals.

15

7. The photoelectric conversion device according to claim 1, wherein, to the circuit element, an accumulation circuit for accumulating a reset noise and a noise-reduction circuit for reducing the reset noise is connected.

20

8. The photoelectric conversion device according to claim 1, wherein the conductor have a width smaller than the width of the wiring.

25

9. The photoelectric conversion device according to claim 1, wherein the conductor have a width larger

than the width of the wiring.

10. The photoelectric conversion device according
to claim 1, which further comprises a terminal
5 connected to a power source for keeping the conductor
at a stated potential.

11. An image sensor comprising:
a light source;
10 an imaging device; and
the photoelectric conversion device according to
claim 1.

12. The image sensor according to claim 11,
15 wherein the photoelectric conversion device is provided
in plurality in a one-dimensional fashion or staggered
fashion on a mounting substrate.

13. The image sensor according to claim 11, which
20 further comprises a wiring for supplying a reference
voltage for keeping the conductor at a stated
potential.

14. An image input system comprising:
25 an original-holding means for holding an original;
the image sensor according to claim 11; and
a control circuit for controlling the image

sensor.

15. The image input system according to claim 14,
wherein the original-holding means is an original stand
5 having a transparent top surface, or an
original-carrying holding-down member.

16. The image input system according to claim 14,
which further comprises a reference voltage source that
10 supplies a reference voltage for keeping the conductor
at a stated potential.

17. The photoelectric conversion device according
to any one of claims 1 to 3, wherein the conductor
15 extends into a substantially square opening formed in a
light-screening layer to define the pixel region, and
along the wiring located inside the pixel region.